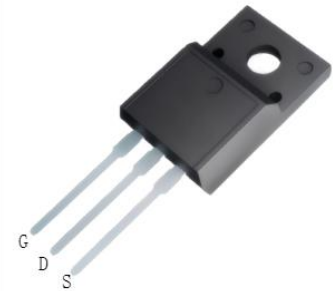
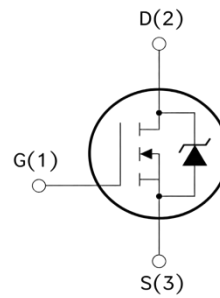


Silicon Carbide Power MOSFET

Parameter	Value	Unit
V_{DS}	650	V
I_D	28	A
$R_{DS(ON)}$	125	m Ω
Q_G	33	nC



TO-220F

Features

- High Speed Switching with Low Capacitances
- High Blocking Voltage with Low $R_{DS(on)}$
- Low impedance package with driver source pin
- Easy to parallel and simple to drive

Applications

- Motor Drives
- Battery Chargers
- Photovoltaic-storage-charging
- High Voltage DC/DC Converters
- Switched-Mode Power Supply(SMPS)

Absolute Maximum Ratings (at $T_J=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Value	Unit
Drain-source Voltage	V_{DS}	$V_{GS}=0V$	650	V
Gate-source Voltage	V_{GS}	Absolute maximum values	-10/+22	V
	V_{GSop}	Recommended operational values	0/+18	
Drain Current (continuous)	I_D	$V_{GS}=15V; T_C=25^\circ\text{C}$	28	A
		$V_{GS}=15V; T_C=100^\circ\text{C}$	22	
Drain Current (pulsed)	I_{DM}	$V_{GS}=15V; T_C=25^\circ\text{C}$	56	A
Power Dissipation	P_D	$T_C=25^\circ\text{C}; T_J=175^\circ\text{C}$	42	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-	-55 to +175	$^\circ\text{C}$
Thermal Resistance from Junction to Case	$R_{\theta JC}$	-	3.55	$^\circ\text{C}/\text{W}$

Electrical Characteristics

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Static characteristics (at $T_C=25^\circ\text{C}$ unless otherwise specified)						
Drain-Source Breakdown Voltage	$B_{V_{DS}}$	$V_{GS}=0V; I_D=500\mu A$	650	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}; I_{DS}=5.2mA$	2.7	-	4.5	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=650V; V_{GS}=0V; T_J=25^\circ\text{C}$	-	-	10	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=18V; V_{DS}=0V$	-	-	250	nA
Static Drain-Source on Resistance	$R_{DS(on)}$	$V_{GS}=15V; I_D=12A$	-	125	165	m Ω
		$V_{GS}=15V; I_D=12A; T_J=175^\circ\text{C}$	-	110	-	
		$V_{GS}=18V; I_D=12A$	-	93	-	
		$V_{GS}=18V; I_D=12A; T_J=175^\circ\text{C}$	-	90	-	
Dynamic characteristics (at $T_C=25^\circ\text{C}$ unless otherwise specified)						
Input Capacitance	C_{iss}	$V_{DS}=500V; f=100KHz; V_{GS}=0V; T_J=25^\circ\text{C}$	-	739	-	pF
Output Capacitance	C_{oss}		-	58	-	
Reverse Transfer Capacitance	C_{rss}		-	4.5	-	
Total Gate Charge	Q_G	$V_{DS}=500V; V_{GS}=0/+15V; I_D=12A; T_J=25^\circ\text{C}$	-	33	-	nC
Gate-Source Charge	Q_{GS}		-	33	-	
Gate-Drain Charge	Q_{GD}		-	13	-	
Gate Resistor	R_G	$f=1MHz; V_{AC}=25mV$	-	3.5	-	Ω
Turn-on Delay Time	$t_{d(on)}$	$V_{DS}=500V; V_{GS}=0/+15V; I_D=12A; R_{g(ext)}=2\Omega$	-	16	-	ns
Rise Time	t_r		-	48	-	
Turn-off Delay Time	$t_{d(off)}$		-	21	-	
Fall Time	t_f		-	34	-	

Reverse SiC Diode Characteristics(at $T_J=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Values			Units
			Min.	Typ.	Max.	
Diode Forward Voltage	V_{FSD}	$V_{GS}=0V; I_F=6A; T_J=25^\circ\text{C}$	-	3.2	-	V
Continuous Diode Forward Current	I_S	$V_{GS}=0V; T_J=25^\circ\text{C}$	-	6	-	A
Reverse Recovery Time	t_{RR}	$V_R=500V; V_{GS}=0V; I_F=12A; di/dt=1200A/\mu s; T_J=25^\circ\text{C}$	-	14	-	ns
Reverse Recovery Charge	Q_{RR}		-	56	-	nC
Peak Reverse Recovery Current	I_{RRM}		-	6.5	-	A

Typical Characteristics

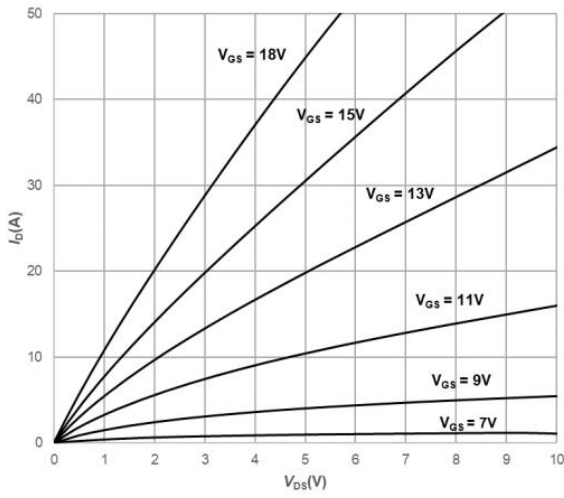


Fig1. Output Characteristics $T_j=25^\circ\text{C}$

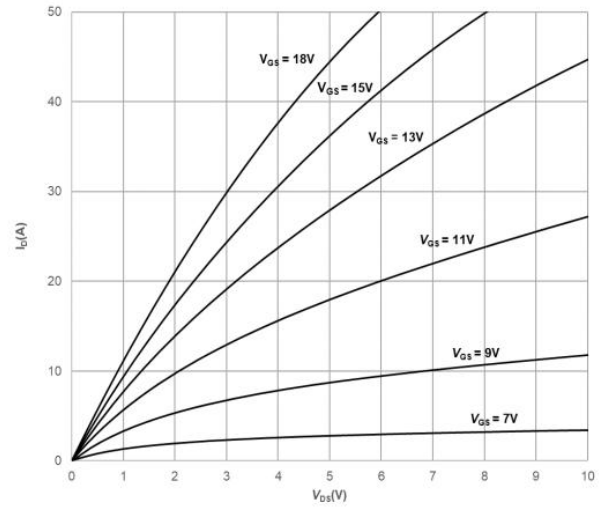


Fig2. Output Characteristics $T_j=175^\circ\text{C}$

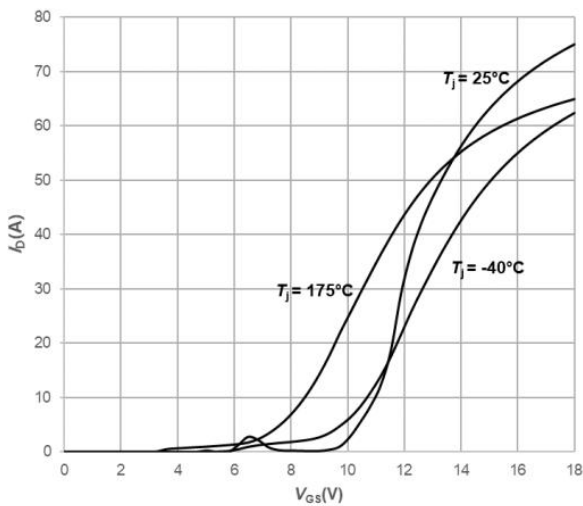


Fig3. Typical Transfer Characteristics

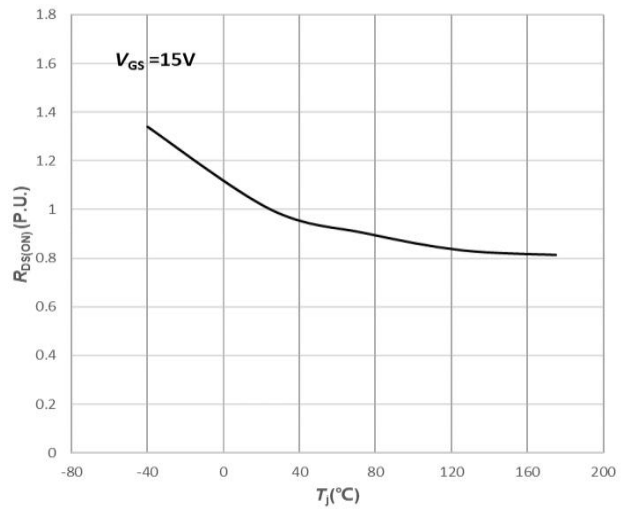


Fig4. Normalized On-Resistance vs. Temperature

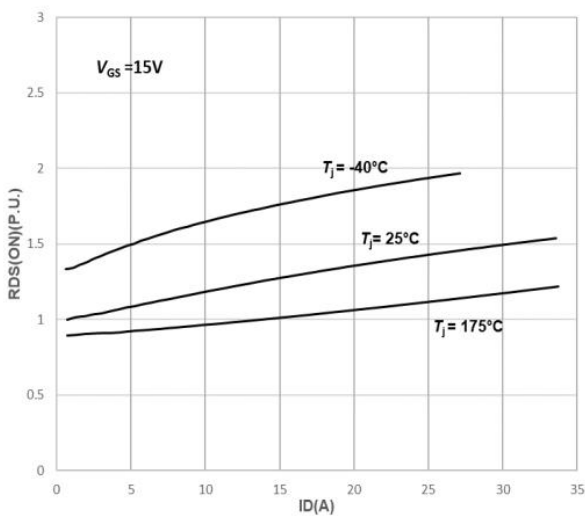


Fig5. Normalized On-Resistance vs. Drain Current For Various Temperatures

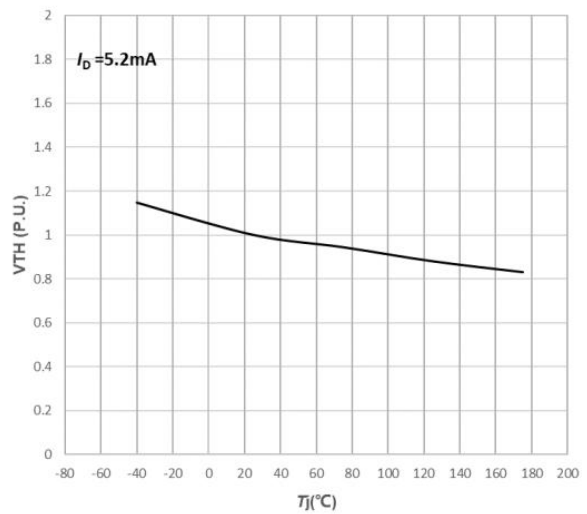


Fig6. Normalized Threshold Voltage vs. Temperature

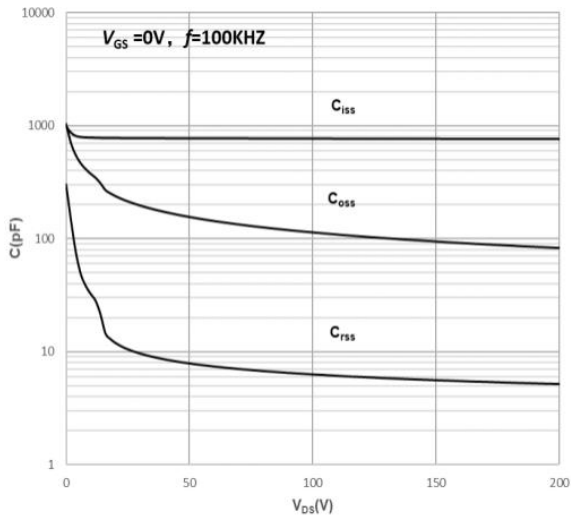


Fig7. Capacitances vs. Drain-Source Voltage (0-200V)

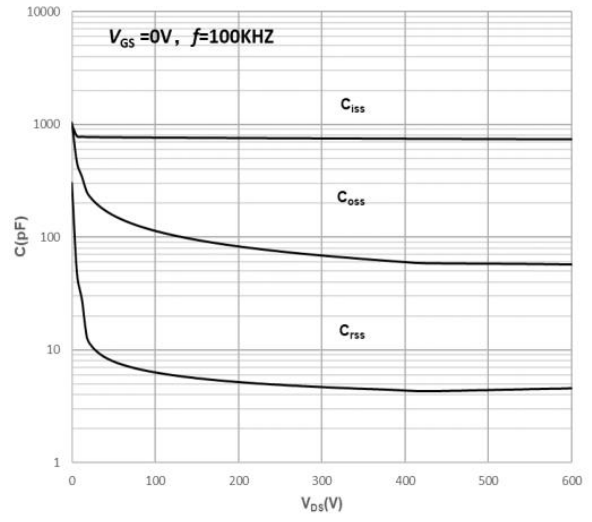


Fig8. Capacitances vs. Drain-Source Voltage (0-600V)

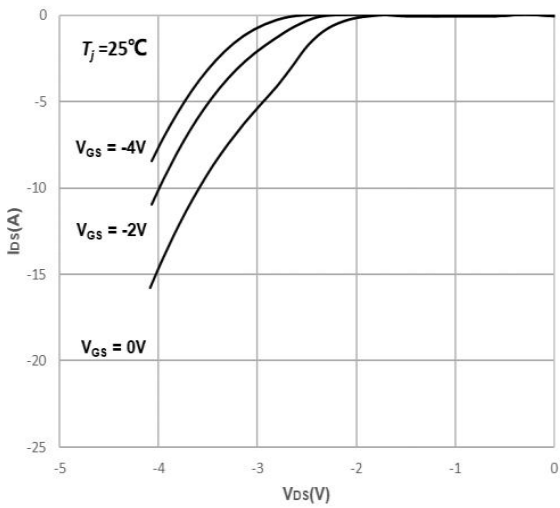
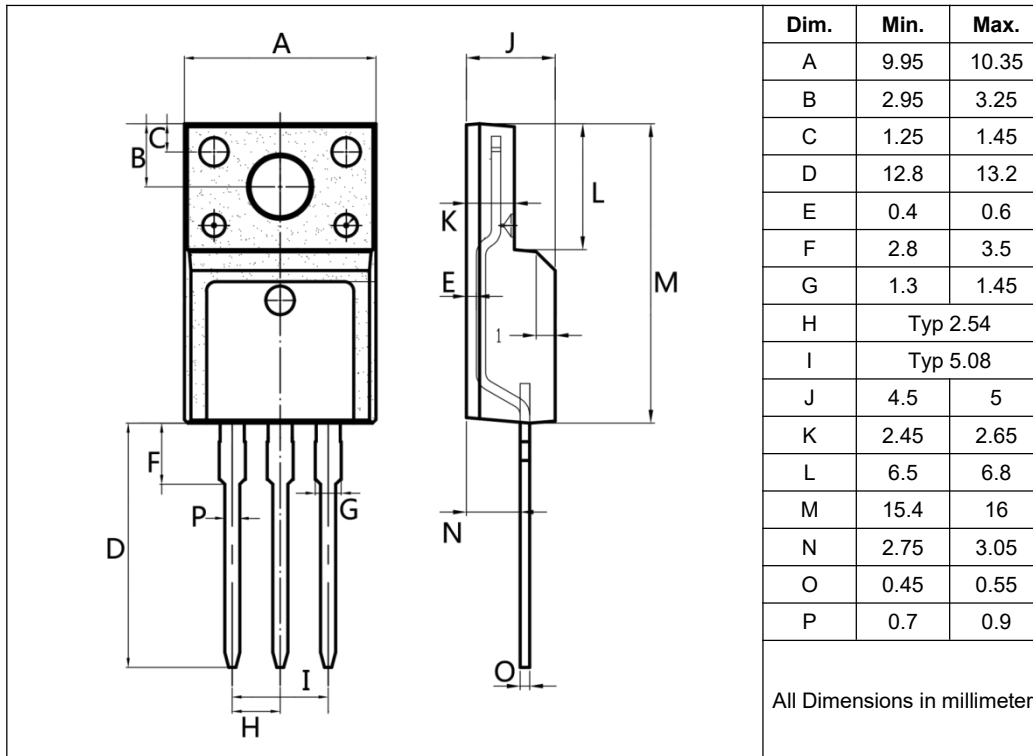


Fig9. Body Diode Characteristics

Package Outlines(Unit:mm)

TO-220F



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